

# BC856BDW1T1, BC857BDW1T1 Series, BC858BDW1T1 Series

Preferred Devices

## Dual General Purpose Transistors

### PNP Duals

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

- Device Marking:  
BC856BDW1T1 = 3B  
BC857BDW1T1 = 3F  
BC857CDW1T1 = 3G  
BC858BDW1T1 = 3K  
BC858CDW1T1 = 3L

#### MAXIMUM RATINGS

Rating	Symbol	BC856	BC857	BC858	Unit
Collector-Emitter Voltage	$V_{CEO}$	-65	-45	-30	V
Collector-Base Voltage	$V_{CBO}$	-80	-50	-30	V
Emitter-Base Voltage	$V_{EBO}$	-5.0	-5.0	-5.0	V
Collector Current - Continuous	$I_C$	-100	-100	-100	mAdc

#### THERMAL CHARACTERISTICS

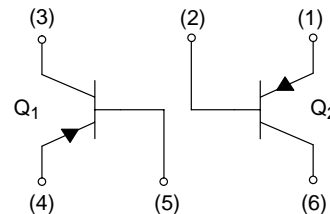
Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above $25^\circ\text{C}$	$P_D$	380 250 3.0	mW  mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in

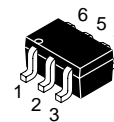


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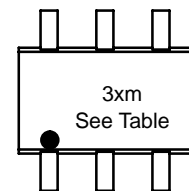
<http://onsemi.com>



#### DEVICE MARKING



SOT-363/SC-88  
CASE 419B  
Style 1



3x = Specific Device Code  
x = B, F, G, K, L  
M = Date Code

#### ORDERING INFORMATION

Device	Package	Shipping†
BC856BDW1T1	SOT-363	3000 Units/Reel
BC857BDW1T1	SOT-363	3000 Units/Reel
BC857CDW1T1	SOT-363	3000 Units/Reel
BC858BDW1T1	SOT-363	3000 Units/Reel
BC858CDW1T1	SOT-363	3000 Units/Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

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## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = –10 mA)	V <sub>(BR)CEO</sub>	–65 –45 –30	–	–	V
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = –10 μA, V <sub>EB</sub> = 0)	V <sub>(BR)CES</sub>	–80 –50 –30	–	–	V
Collector–Base Breakdown Voltage (I <sub>C</sub> = –10 μA)	V <sub>(BR)CBO</sub>	–80 –50 –30	–	–	V
Emitter–Base Breakdown Voltage (I <sub>E</sub> = –1.0 μA)	V <sub>(BR)EBO</sub>	–5.0 –5.0 –5.0	–	–	V
Collector Cutoff Current (V <sub>CB</sub> = –30 V) (V <sub>CB</sub> = –30 V, T <sub>A</sub> = 150°C)	I <sub>CBO</sub>	–	–	–15 –4.0	nA μA

## ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = –10 μA, V <sub>CE</sub> = –5.0 V)	h <sub>FE</sub>	–	150	–	–
		–	270	–	–
(I <sub>C</sub> = –2.0 mA, V <sub>CE</sub> = –5.0 V)		220	290	475	
		420	520	800	
Collector–Emitter Saturation Voltage (I <sub>C</sub> = –10 mA, I <sub>B</sub> = –0.5 mA)	V <sub>CE(sat)</sub>	–	–	–0.3	V
(I <sub>C</sub> = –100 mA, I <sub>B</sub> = –5.0 mA)		–	–	–0.65	
Base–Emitter Saturation Voltage (I <sub>C</sub> = –10 mA, I <sub>B</sub> = –0.5 mA)	V <sub>BE(sat)</sub>	–	–0.7	–	V
(I <sub>C</sub> = –100 mA, I <sub>B</sub> = –5.0 mA)		–	–0.9	–	
Base–Emitter On Voltage (I <sub>C</sub> = –2.0 mA, V <sub>CE</sub> = –5.0 V)	V <sub>BE(on)</sub>	–0.6	–	–0.75	V
(I <sub>C</sub> = –10 mA, V <sub>CE</sub> = –5.0 V)		–	–	–0.82	

## SMALL–SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product (I <sub>C</sub> = –10 mA, V <sub>CE</sub> = –5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	100	–	–	MHz
Output Capacitance (V <sub>CB</sub> = –10 V, f = 1.0 MHz)	C <sub>ob</sub>	–	–	4.5	pF
Noise Figure (I <sub>C</sub> = –0.2 mA, V <sub>CE</sub> = –5.0 Vdc, R <sub>S</sub> = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)	NF	–	–	10	dB

TYPICAL CHARACTERISTICS – BC856

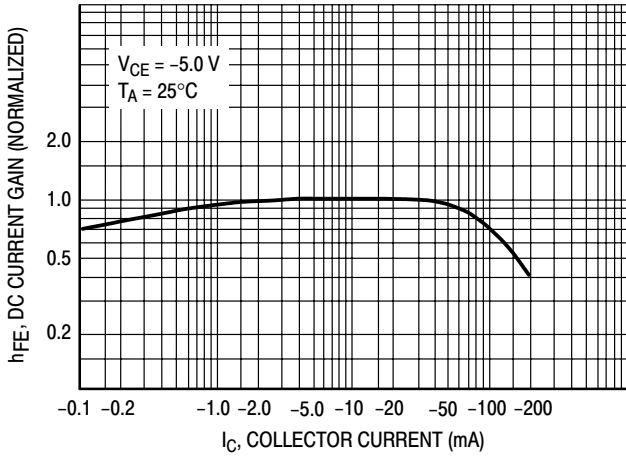


Figure 1. DC Current Gain

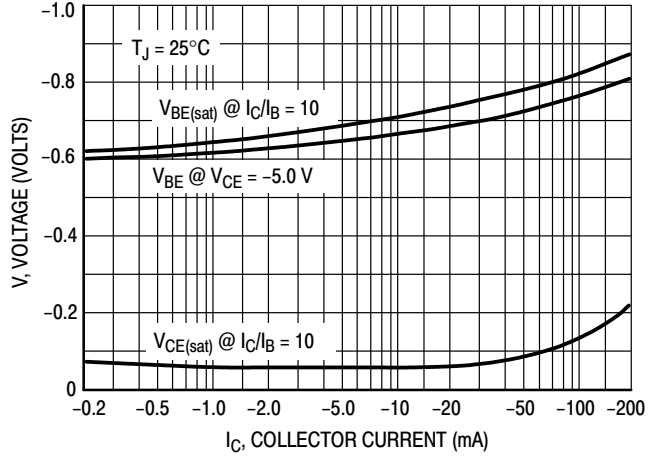


Figure 2. "On" Voltage

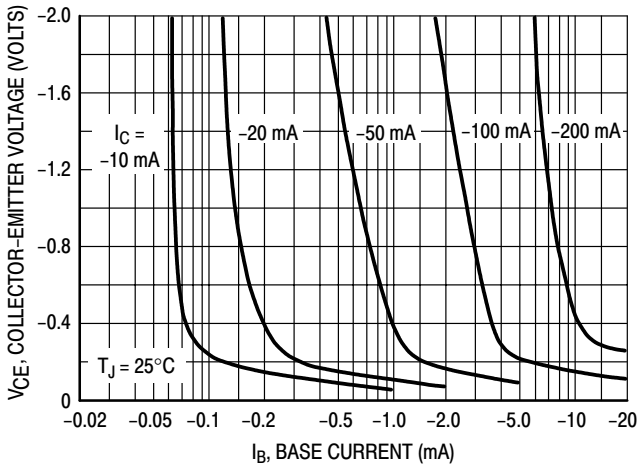


Figure 3. Collector Saturation Region

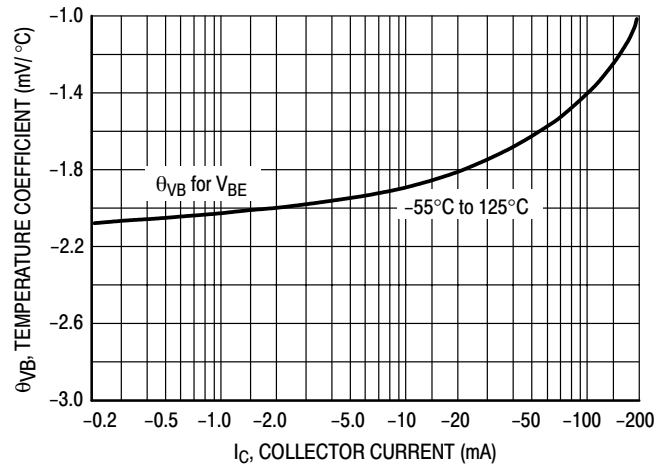


Figure 4. Base-Emitter Temperature Coefficient

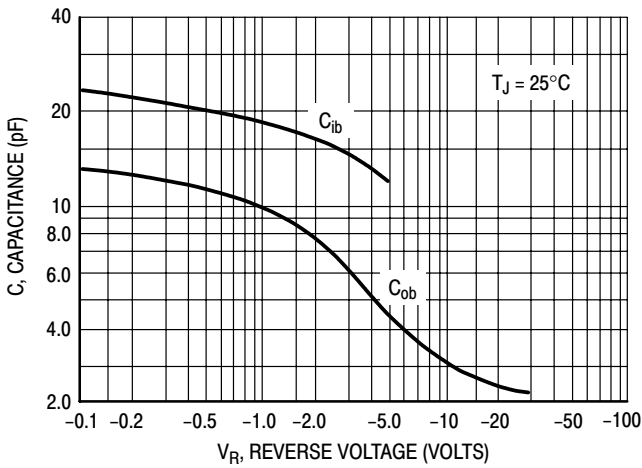


Figure 5. Capacitance

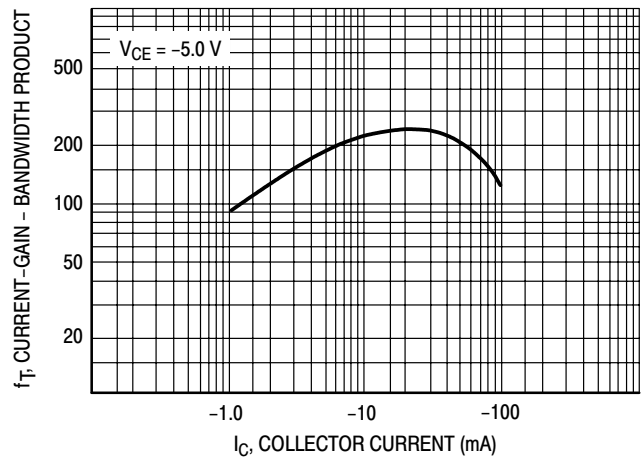


Figure 6. Current-Gain - Bandwidth Product

TYPICAL CHARACTERISTICS – BC857/BC858

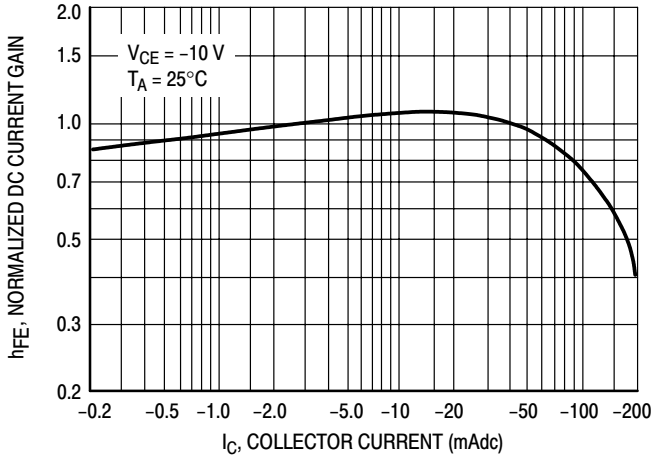


Figure 7. Normalized DC Current Gain

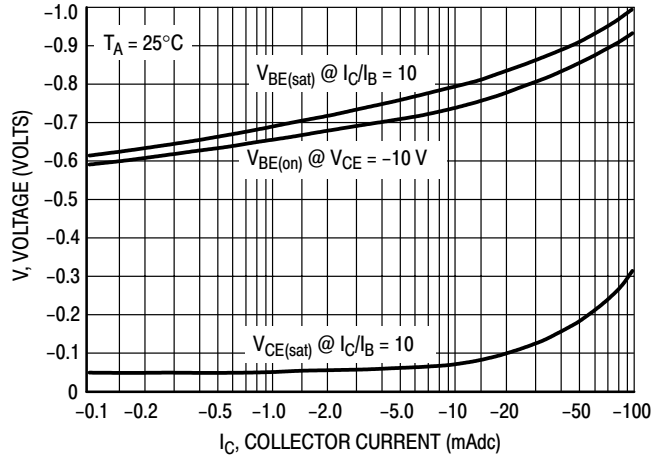


Figure 8. "Saturation" and "On" Voltages

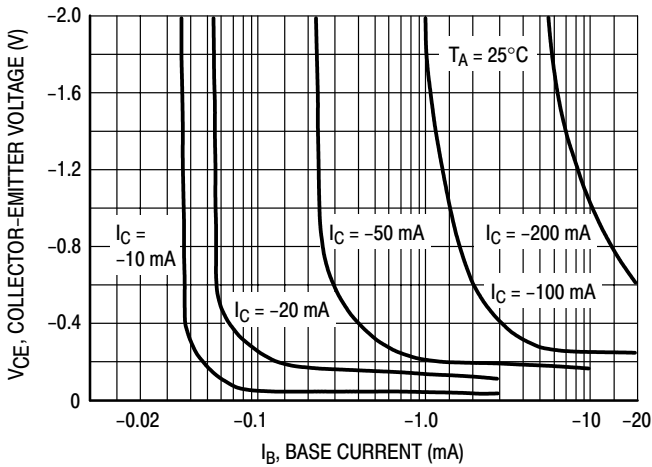


Figure 9. Collector Saturation Region

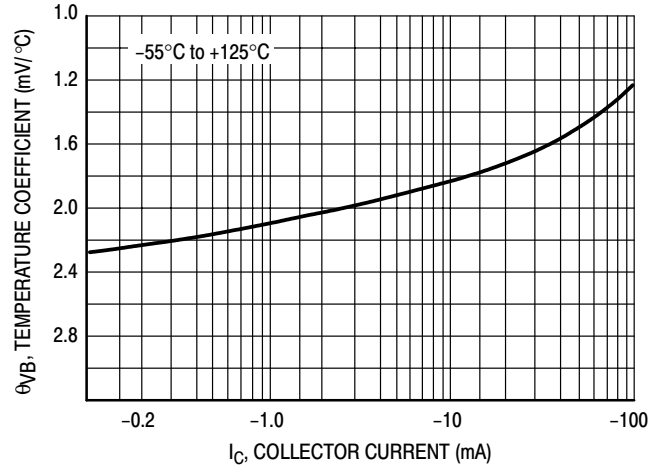


Figure 10. Base-Emitter Temperature Coefficient

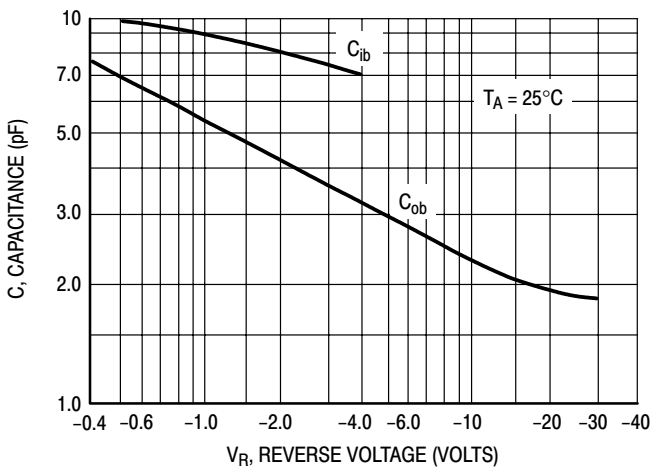


Figure 11. Capacitances

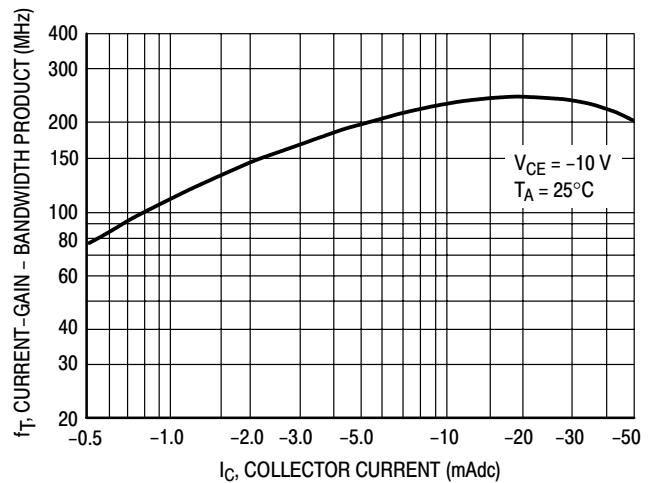
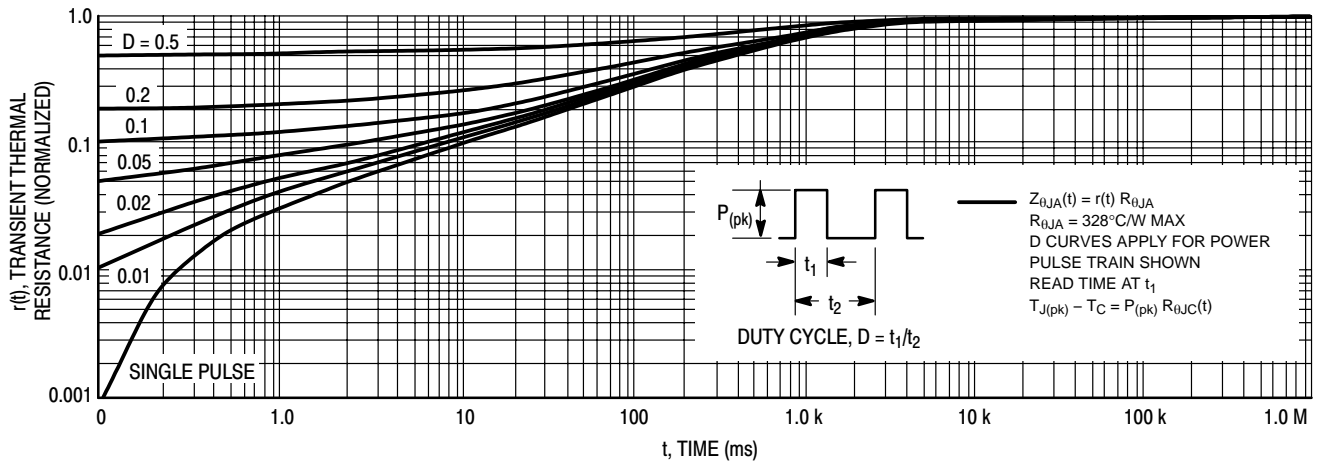
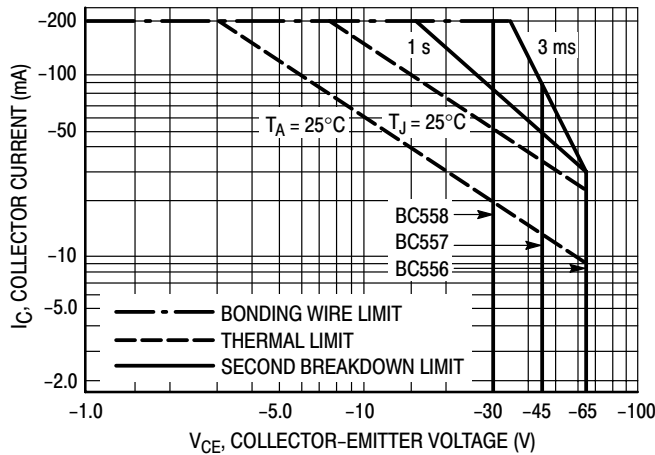


Figure 12. Current-Gain - Bandwidth Product

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**Figure 13. Thermal Response**



**Figure 14. Active Region Safe Operating Area**

The safe operating area curves indicate  $I_C$ - $V_{CE}$  limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

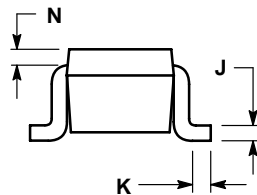
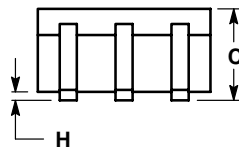
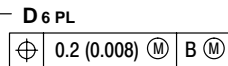
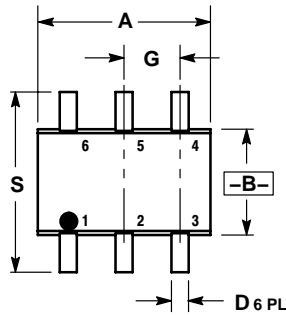
The data of Figure 14 is based upon  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  or  $T_A$  is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

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## PACKAGE DIMENSIONS

### SC-88 (SOT-363) CASE 419B-02 ISSUE T

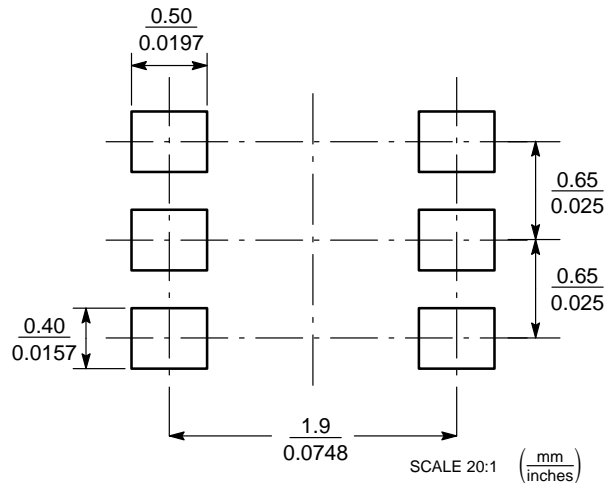
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20

- STYLE 1:  
PIN 1. EMITTER 2  
2. BASE 2  
3. COLLECTOR 1  
4. EMITTER 1  
5. BASE 1  
6. COLLECTOR 2

### SOLDERING FOOTPRINT\*



SC-88/SC70-6

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